

100V N-Channel Enhancement Mode MOSFET

Voltage

Current 56 A

Features

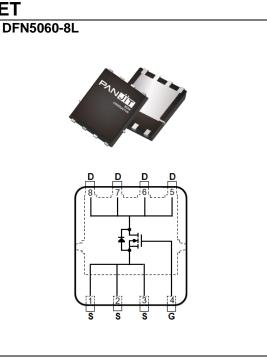
• $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A<11m\Omega$

100 V

- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@10A < 16m\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN5060-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	100	- v	
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current ^(Note 3)	Tc=25°C	- I _D -	56		
	$T_{C}=100^{\circ}C$		40	А	
Pulsed Drain Current ^(Note 1)	Tc=25°C	I _{DM}	224		
Power Dissipation	Tc=25°C	Da	68	w	
	$T_{C}=100^{\circ}C$	Po	34		
Continuous Drain Current ^(Note 4)	T _A =25°C		12.4	A	
	T _A =70 [°] C	I _D	10.4		
Power Dissipation	T _A =25 [°] C	Po	3.3	w	
	T _A =70 [°] C		2.3		
Single Pulse Avalanche Current ^(Note 5)		las	18	А	
Single Pulse Avalanche Energy ^(Note 5)		Eas	28	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	2.2	°C/W	
	Junction to Ambient	R _{0JA}	45		



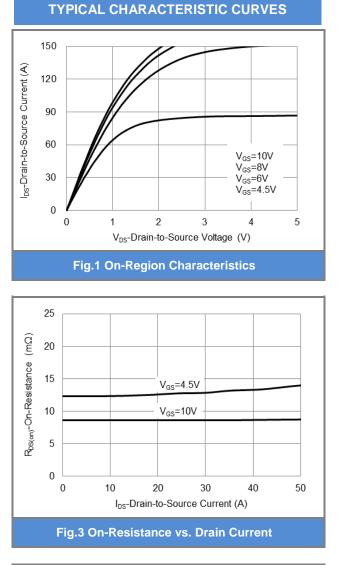
Electrical Characteristics (TA=25°C unless otherwise noted)

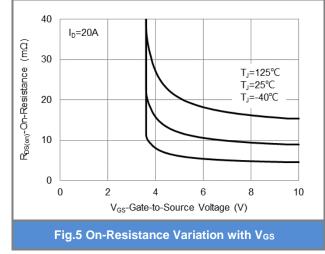
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static		·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	-	-	v	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.5	1.9	3		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	8.4	11		
		V _{GS} =4.5V, I _D =10A	- 12 1		16	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =100V, V_{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
Dynamic ^(Note 6)	-	-	-	-	•	-	
Total Gate Charge	Qg		-	35	-		
Gate-Source Charge	Qgs	V _{DS} =50V, I _D =20A, V _{GS} =10V	-	7	-	nC	
Gate-Drain Charge	Q _{gd}	VGS=10V	-	10	-		
Input Capacitance	Ciss		-	1459	-	pF	
Output Capacitance	Coss	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	272	-		
Reverse Transfer Capacitance	Crss	T=TMHZ	-	15	-		
Gate resistance	Rg	f=1MHz	-	0.84	-	Ω	
Turn-On Delay Time	td(on)		-	8	-		
Turn-On Rise Time	tr	V _{DS} =50V, I _D =20A,	-	20	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_G=3\Omega$	-	27	-	ns	
Turn-Off Fall Time	tf		-	21	-		
Drain-Source Diode	-				-		
Diode Forward Current	I _S	Tc=25°C	-	-	56	_	
Pulsed Diode Forward Current	I _{SM}	1c=25 C	-	-	224	A	
Diode Forward Voltage	V _{SD}	Is=20A, V _{GS} =0V	-	0.85	1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	39	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	31	-	nC	

NOTES :

- 1. Pulse width100us, Duty cycle<2%.</td>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an $R_{\theta JC}=2.2^{\circ}C/W$.
- 4. $R_{\theta,JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. E_{AS} is calculated based on the condition of L=1mH, I_{AS}=7.5A, V_{DD}=30V, V_{GS}=10V. 100% test at L=0.1mH, I_{AS}=18A in production.
- 6. Guaranteed by design, not subject to production testing.

PJQ5574A-AU





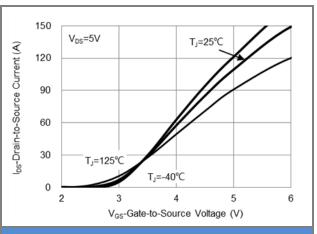


Fig.2 Transfer Characteristics

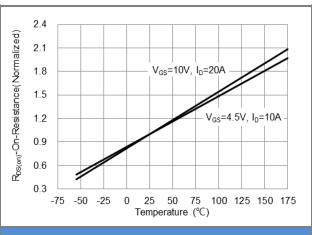
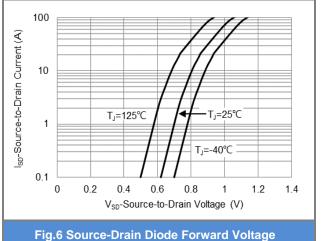


Fig.4 On-Resistance vs. Junction temperature



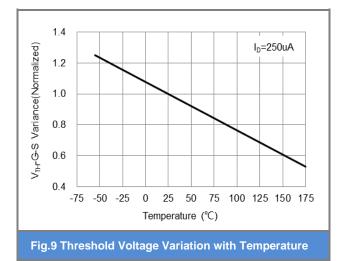
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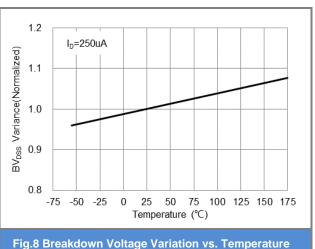
CONDUCTOR PJQ5574A-AU

SEM

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TYPICAL CHARACTERISTIC CURVES 10 V_{DS}=50V I_D=20A V_{GS}-Gate-to-Source Voltage (V) 8 6 4 2 0 0 8 16 24 32 40 Qg (nC) Fig.7 Gate-Charge Characteristics







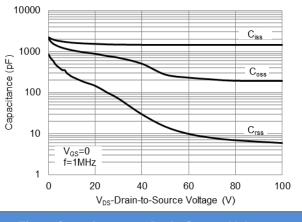
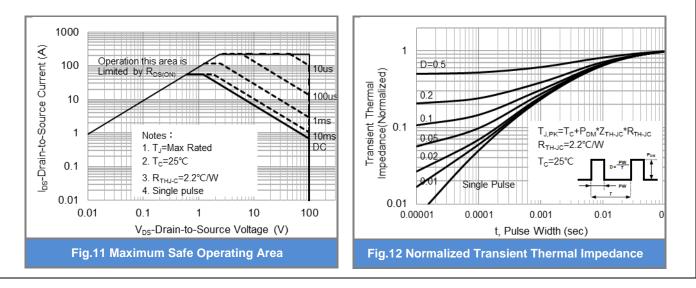


Fig.10 Capacitance vs. Drain-Source Voltage

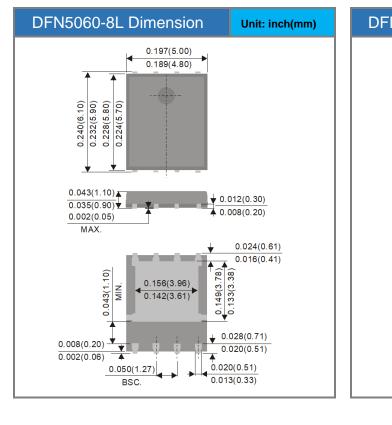


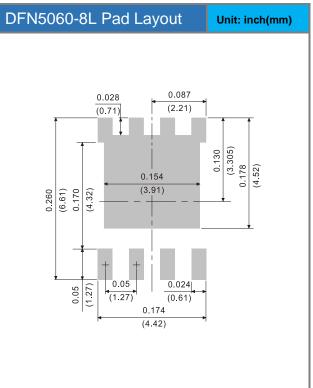


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ5574A-AU	DFN5060-8L	3K pcs / 13" reel	Q5574A	

Packaging Information & Mounting Pad Layout







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